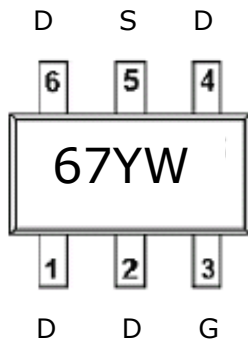
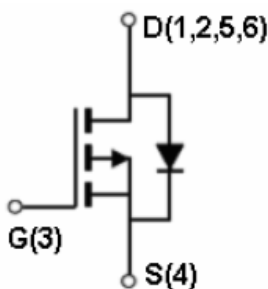


**DESCRIPTION**

The STP3467 is the P-Channel enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application, such as cellular phone and notebook computer power management and other battery powered circuits, and low in-line power loss are needed in a very small outline surface mount package.

**PIN CONFIGURATION  
TSOP-6P**


**Y: Year**  
**A: Week Code**


**FEATURE**

- ◆ -20V/-5.0A,  $R_{DS(ON)}=90\text{mohm}@V_{GS}=-4.5\text{V}$
- ◆ -20V/-3.5A,  $R_{DS(ON)}=110\text{mohm}@V_{GS}=-2.5\text{V}$
- ◆ -20V/-1.7A,  $R_{DS(ON)}=140\text{mohm}@V_{GS}=-1.8\text{V}$
- ◆ Super high density cell design for extremely low  $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ TSOP-6P package design

**ORDERING INFORMATION**

Part Number	Package	Part Marking
STP3467ST6RG	TSOP-6	67YW

※ Week Code Code : A ~ Z ; a ~ z

※ STP3467ST6RG ST6 : TSOP-6; R: Tape Reel ; G: Pb - Free



**STP3467** 

P Channel Enhancement Mode MOSFET  
-5.2A

**ABSOLUTE MAXIMUM RATINGS** (Ta = 25°C unless otherwise noted )

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V <sub>DSS</sub>	-20	V
Gate-Source Voltage	V <sub>GSS</sub>	±12	V
Continuous Drain Current (T <sub>J</sub> =150°C)	I <sub>D</sub>	T <sub>A</sub> =25°C	-5.2
		T <sub>A</sub> =70°C	-4.2
Pulsed Drain Current	I <sub>DM</sub>	-20	A
Continuous Source Current (Diode Conduction)	I <sub>S</sub>	-1.7	A
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	2.0
		T <sub>A</sub> =70°C	1.3
Operation Junction Temperature	T <sub>J</sub>	-55/150	°C
Storage Temperature Range	T <sub>STG</sub>	-55/150	°C
Thermal Resistance-Junction to Ambient	R <sub>θJA</sub>	90	°C/W



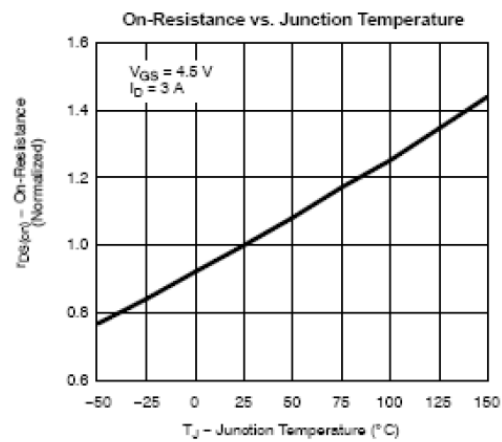
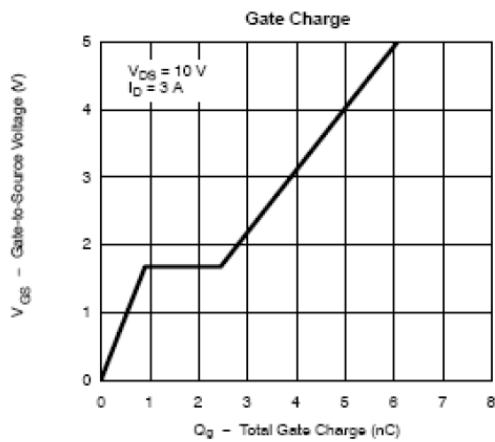
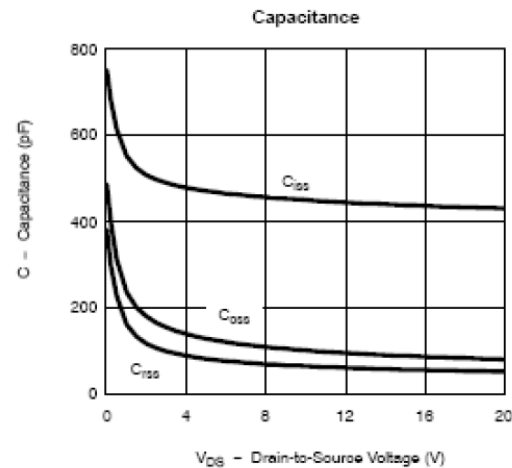
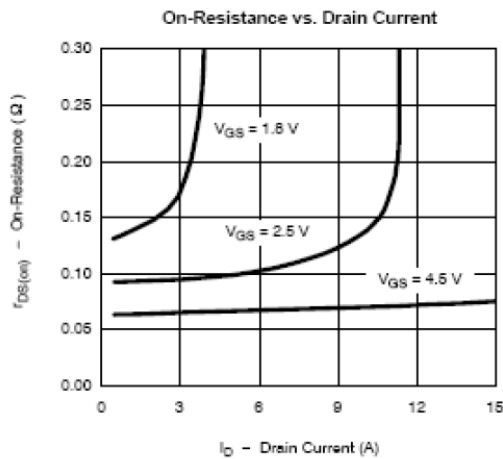
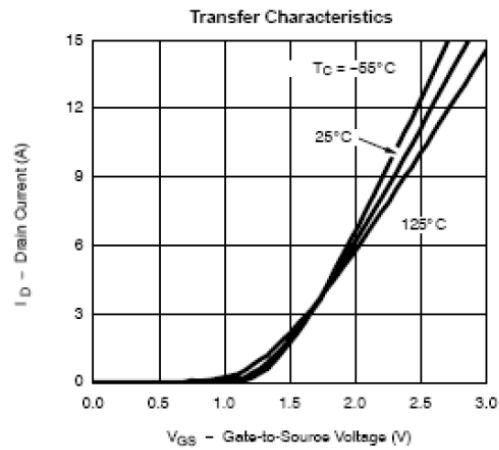
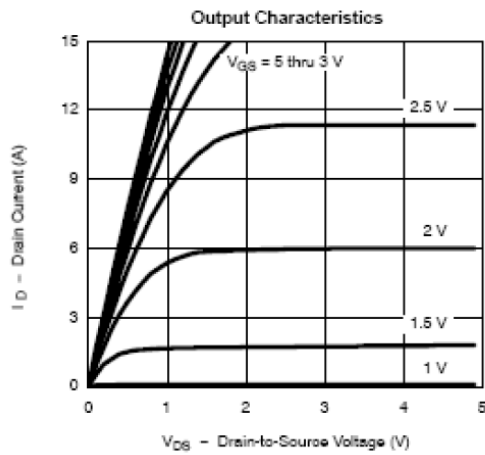
**STP3467** 

P Channel Enhancement Mode MOSFET  
-5.2A

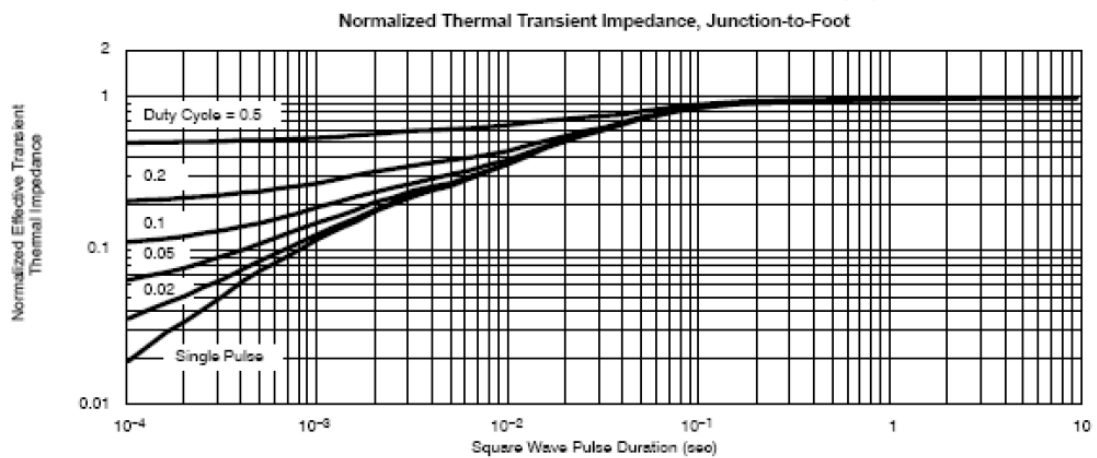
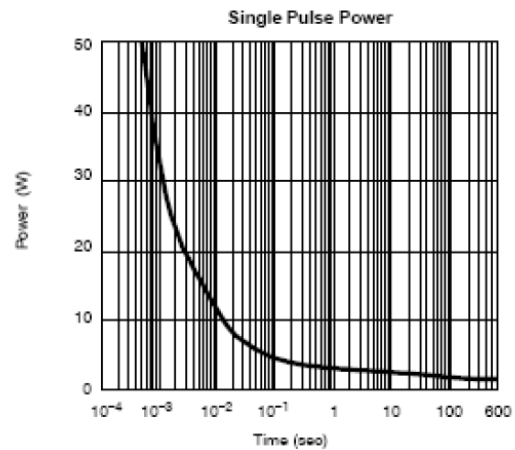
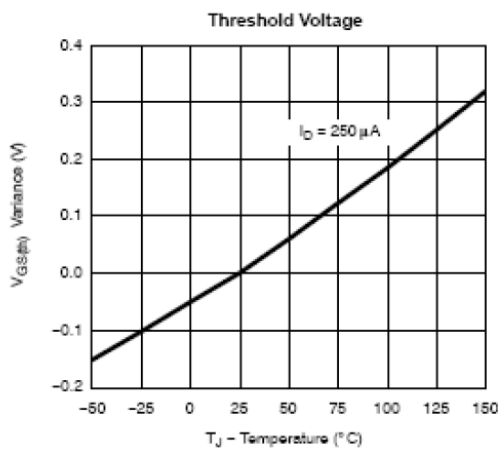
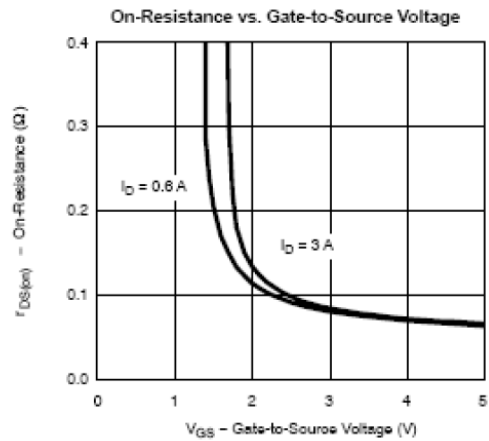
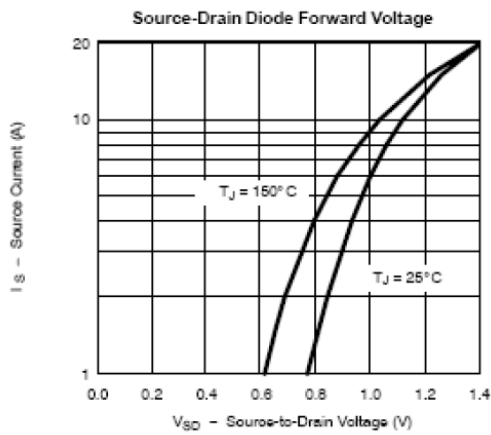
**ELECTRICAL CHARACTERISTICS** ( Ta = 25°C Unless otherwise noted )

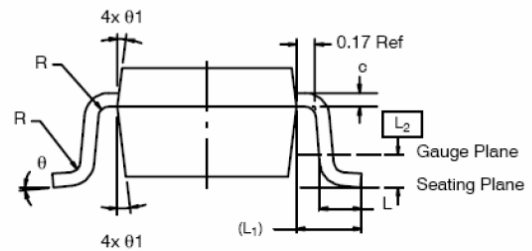
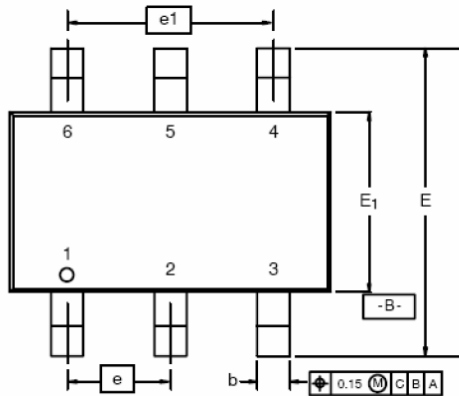
Parameter	Symbol	Condition	Min	Typ	Max	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=-250\mu A$	-20			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=-250\mu A$	-0.35		-0.8	V
Gate Leakage Current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 12V$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=-20V, V_{GS}=0V$			-1	uA
		$V_{DS}=-20V, V_{GS}=0V$ $T_J=55^\circ C$			-5	
On-State Drain Current	$I_{D(on)}$	$V_{DS}\leq -5V, V_{GS}=-10V$	-6			A
Drain-source On-Resistance	$R_{DS(on)}$	$V_{GS}=-10V, I_D=-5.2A$		0.075	0.090	$\Omega$
		$V_{GS}=-4.5V, I_D=-4.2A$		0.090	0.110	
		$V_{GS}=-1.8V, I_D=-1.7A$		0.120	0.140	
Forward Transconductance	$g_{fs}$	$V_{DS}=-5.0V, I_D=-2.8A$		-10		S
Diode Forward Voltage	$V_{SD}$	$I_S=-1.5A, V_{GS}=0V$		-0.8	-1.2	V
<b>Dynamic</b>						
Total Gate Charge	$Q_g$	$V_{DS}=-6V, V_{GS}=-4.5V,$ $V_{DS}=-2.8A$		4.8	8	nC
Gate-Source Charge	$Q_{gs}$			1.0		
Gate-Drain Charge	$Q_{gd}$			1.0		
Input Capacitance	$C_{iss}$	$V_{DS}=-6V, V_{GS}=0,$ $f=1MHz$		485		pF
Output Capacitance	$C_{oss}$			85		
Reverse Transfer Capacitance	$C_{rss}$			40		
Turn-On Time	$T_{d(on)}$	$V_{DD}=-6V,$ $R_L=6\Omega, V_{GEN}=-4.5V$ $R_G=6\Omega$		10	15	ns
	$t_r$			15	25	
Turn-Off Time	$T_{d(off)}$			18	25	
	$t_f$			15	20	

**TYPICAL CHARACTERISTICS**



**TYPICAL CHARACTERISTICS**



**TSOP-6 PACKAGE OUTLINE**


Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.91	-	1.10	0.038	-	0.043
A <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039
b	0.30	0.32	0.45	0.012	0.013	0.018
c	0.10	0.15	0.20	0.004	0.008	0.008
D	2.95	3.05	3.10	0.116	0.120	0.122
E	2.70	2.85	2.98	0.108	0.112	0.117
E <sub>1</sub>	1.55	1.65	1.70	0.081	0.085	0.067
e	1.00 BSC			0.0394 BSC		
e <sub>1</sub>	1.90	2.00	2.10	0.075	0.080	0.085
L	0.35	-	0.50	0.014	-	0.020
L <sub>1</sub>	0.60 Ref			0.024 Ref		
L <sub>2</sub>	0.25 BSC			0.010 BSC		
R	0.10	-	-	0.004	-	-
θ	0°	4°	8°	0°	4°	8°
θ <sub>1</sub>	7° Nom			7° Nom		